

IN THE CLAIMS

Please amend the claims as follows:

1-10. (canceled)

11. (Currently Amended) A process for obtaining a thin layer made of a first material on a substrate made of a second material called a final substrate, the process comprising, in the order as hereinafter set forth:

bonding a thick layer of a first material by one of its main faces on the final substrate at an interface; followed by implanting gaseous species in the thick layer of the first material to create a weakened zone delimiting said thin layer between the interface and the weakened zone, or implanting gaseous species in a thick layer of a first material to create a weakened zone followed by bonding said thick layer of said first material by one of its main faces on the final substrate at an interface thereby delimiting said thin layer between the interface and the weakened zone;

depositing a layer of a third material ~~called~~ to form a self-supporting layer on a free face of the thick layer made of the first material; and

fracturing ~~within~~ the structure ~~composed of~~ comprising the final substrate, the thick layer of the first material and the layer of the third material; at the weakened zone to supply the substrate supporting said thin layer.

12. (Previously Presented) The process according to claim 11, wherein implanting gaseous species further comprises implanting one or more identical or different gaseous species.

13. (Previously Presented) The process according to claim 12, wherein said gaseous species ~~is~~ are selected from the group consisting of a hydrogen and a helium.

14. (Currently Amended) ~~The process according to claim 11,~~ A process for obtaining a thin layer made of a first material on a substrate made of a second material called a final substrate, the process comprising: bonding a thick layer of a first material by one of its main faces on the final substrate at an interface; implanting gaseous species in the thick layer of the first material to create a weakened zone delimiting said thin layer between the interface and the weakened zone; depositing a layer of a third material called a self-supporting layer on a free face of the thick layer made of the first material; and fracturing within the structure composed of the final substrate, the thick layer of the first material and the layer of the third material, at the weakened zone to supply the substrate supporting said thin layer,

wherein the thick layer of the first material is a layer delimited in an initial substrate when implanting a gaseous species to create a weakened zone in the initial substrate, and further comprising fracturing between the thick layer of the first material and a remainder of the initial substrate, which is performed after bonding the thick layer of the first material onto the final substrate.

15. (Previously Presented) The process according to claim 14, wherein implanting gaseous species in the initial substrate further comprises implanting hydrogen ions.

16. (Previously Presented) The process according to claim 14, wherein implanting gaseous species in the thick layer of the first material is performed after fracturing between the thick layer of the first material and a remainder of the initial substrate.

17. (Previously Presented) The process according to claim 14, wherein implanting gaseous species in the thick layer of first material is performed before bonding the thick layer of the first material on the final substrate.

18. (Previously Presented) The process according to claim 17, wherein fracturing is performed by a heat treatment, wherein implanting gaseous species is performed under conditions so that the fracturing between the thick layer of the first material and a remainder of the initial substrate is obtained at a temperature less than the fracture temperature of said structure.

19. (Previously Presented) The process according to claim 11, wherein the thick layer of the first material is bonded onto the final substrate by molecular bonding.

20. (Previously Presented) The process according to claim 11, wherein a part of the self-supporting layer is deposited, and the gaseous species are implanted in the thick layer of the first material after the partial deposit.

21. (New) The process according to claim 11, wherein said thin layer has a thickness less than 0.1 μm .

22. (New) The process according to claim 14, wherein said thin layer has a thickness less than 0.1 μm .

23. (New) The process according to claim 11, comprising, in the order as hereinafter set forth:

bonding a thick layer of a first material by one of its main faces on the final substrate at an interface followed by implanting gaseous species in the thick layer of the first material to create a weakened zone delimiting said thin layer between the interface and the weakened zone;

depositing a layer of a third material to form a self-supporting layer on a free face of the thick layer made of the first material; and

fracturing the structure comprising the final substrate, the thick layer of the first material and the layer of the third material at the weakened zone to supply the substrate supporting said thin layer.

24. (New) The process according to claim 23, wherein implanting gaseous species further comprises implanting one or more identical or different gaseous species.

25. (New) The process according to claim 24, wherein said gaseous species are selected from the group consisting of hydrogen and helium.

26. (New) The process according to claim 11, comprising, in the order as hereinafter set forth:

implanting gaseous species in a thick layer of a first material to create a weakened zone followed by bonding said thick layer of said first material by one of its main faces on the final substrate at an interface thereby delimiting said thin layer between the interface and the weakened zone;

depositing a layer of a third material to form a self-supporting layer on a free face of the thick layer made of the first material; and

fracturing the structure comprising the final substrate, the thick layer of the first material and the layer of the third material at the weakened zone to supply the substrate supporting said thin layer.

27. (New) The process according to claim 26, wherein implanting gaseous species further comprises implanting one or more identical or different gaseous species.

28. (New) The process according to claim 12, wherein said gaseous species are selected from the group consisting of hydrogen and helium.

29. (New) The process according to claim 11, consisting of, in the order as hereinafter set forth:

bonding a thick layer of a first material by one of its main faces on the final substrate at an interface followed by implanting gaseous species in the thick layer of the first material to create a weakened zone delimiting said thin layer between the interface and the weakened zone;

depositing a layer of a third material to form a self-supporting layer on a free face of the thick layer made of the first material; and

fracturing the structure comprising the final substrate, the thick layer of the first material and the layer of the third material at the weakened zone to supply the substrate supporting said thin layer.

30. (New) The process according to claim 11, consisting of, in the order as hereinafter set forth:

implanting gaseous species in a thick layer of a first material to create a weakened zone followed by bonding said thick layer of said first material by one of its main faces on the final substrate at an interface thereby delimiting said thin layer between the interface and the weakened zone;

depositing a layer of a third material to form a self-supporting layer on a free face of the thick layer made of the first material; and

fracturing the structure comprising the final substrate, the thick layer of the first material and the layer of the third material at the weakened zone to supply the substrate supporting said thin layer.